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Attorney's Docket No.: 12732-092002 / US5564/5995D1



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Shunpei Yamazaki et al. Art Unit : 2811  
Serial No. : 10/718,584 Examiner : Unknown  
Filed : November 24, 2003 Confirmation No.: 1684  
Title : SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

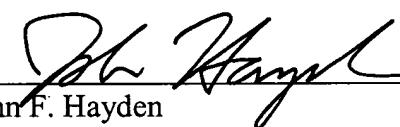
MAIL STOP AMENDMENT  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**INFORMATION DISCLOSURE STATEMENT**

Applicants submit the references listed on the attached form PTO-1449. In accordance with the PTO's waiver of 37 CFR 1.98 (a)(2)(iii), only copies of foreign patent documents and non-patent references are enclosed.

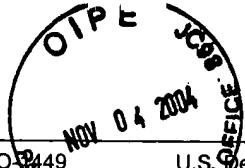
This statement is being filed before the receipt of a first Office Action on the merits.  
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Respectfully submitted,

  
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Date: November 4, 2004

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Substitute Form PTO-1449 (Modified)		U.S. Department of Commerce Patent and Trademark Office		Attorney's Docket No. 12732-092002	Application No. 10/718,584
<b>Information Disclosure Statement</b> <b>by Applicant</b> (Use several sheets if necessary) (37 CFR §1.98(b))		Applicant		Shunpei Yamazaki et al.	
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U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA	3,108,914	10/29/1963	Hoerni			
	AB	3,791,883	02/12/1974	Takei et al.			
	AC	4,309,224	01/05/1982	Shibata			
	AD	4,330,363	05/18/1982	Biegesen et al.			
	AE	4,502,204	03/05/1985	Togashi et al.			
	AF	4,727,044	02/23/1988	Yamazaki			
	AG	4,851,363	07/25/1989	Troxell et al.			
	AH	4,915,772	04/10/1990	Fehlner et al.			
	AI	5,075,259	12/24/1991	Moran			
	AJ	5,108,843	04/28/1992	Ohtaka et al.			
	AK	5,147,826	09/15/1992	Liu et al.			
	AL	5,219,786	06/15/1993	Noguchi			
	AM	5,244,836	09/14/1993	Lim			
	AN	5,248,630	09/28/1993	Serikawa et al.			
	AO	5,273,920	12/28/1993	Kwasnick et al.			
	AP	5,278,093	01/11/1994	Yonehara			
	AQ	5,289,030	02/22/1994	Yamazaki et al.			
	AR	5,311,041	05/10/1994	Tominaga et al.			
	AS	5,352,291	10/04/1994	Zhang et al.			
	AT	5,387,530	02/07/1995	Doyle et al.			
	AU	5,403,772	04/04/1995	Zhang et al.			
	AV	5,426,064	06/20/1995	Zhang et al.			
	AW	5,481,121	01/02/1996	Zhang et al.			
	AX	5,529,937	06/25/1996	Zhang et al.			
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	AZ	5,639,698	06/17/1997	Yamazaki et al.			
	AAA	5,710,050	01/20/1998	Makita et al.			

Examiner Signature	Date Considered
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

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U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	ABB	5,773,327	06/30/1998	Yamazaki et al.			
	ACC	5,843,225	12/01/1998	Takayama et al.			
	ADD	6,168,981 B1	01/02/2001	Battaglia et al.			
	AEE	6,287,988 B1	09/11/2001	Nagamine et al.			
	AFF	6,436,745 B1	08/20/2002	Gotou et al.			
	AGG	US 2002/0164843 (with current claims)	11/07/2002	Yamazaki et al.			
	AHH	US 2003/0060057	03/27/2003	Raaijmakers et al.			

Foreign Patent Documents or Published Foreign Patent Applications							
Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation
							Yes No
	AII	JP 04-011722	01/16/1992	Japan			Full
	AJJ	JP 06-013610	01/21/1994	Japan			Abs
	AKK	JP 06-267978	09/22/1994	Japan			Abs
	ALL	JP 56-024925	03/10/1981	Japan			Abs
	AMM	JP 60-105216	06/10/1985	Japan			Abs

Other Documents (include Author, Title, Date, and Place of Publication)		
Examiner Initial	Desig. ID	Document
	ANN	S. Caune et al.; "Combined CW Laser and Furnace Annealing of Amorphous Si and Ge in Contact with some Metals"; <u>Applied Surface Science</u> , vol. 36, pp. 597-604 (1989)
	AOO	B.C. Ahn et al.; "Batch-Processing of High-Performance Amorphous-Silicon/Silicon-Nitride Thin-Film Transistors" <u>IEEE Display Research Conference</u> , pp. 85-88 (1991)
	APP	Kenji Sera et al.; "High-Performance TFT's Fabricated by XeCl Excimer Laser Annealing of Hydrogenated Amorphous-Silicon Film"; <u>IEEE Transactions On Electron Device</u> , vol. 36, no. 12; pp. 2868-2872 (December 1989)
	AQQ	L. Hultman et al.; "Crystallization of Amorphous Silicon During Thin-film Gold Reaction"; <u>J. Appl. Phys.</u> , vol. 62, no. 9; pp. 3647-3655 (November 1987)
	ARR	Yunosuke Kawazu et al.; "Low-Temperature Crystallization of Hydrogenated Amorphous Silicon Induced by Nickel Silicide Formation"; <u>Japanese Journal of Applied Physics</u> , vol. 29, no. 12; pp. 2698-2704 (1990)

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		Filing Date November 24, 2003	Group Art Unit 2811	

<b>Other Documents (include Author, Title, Date, and Place of Publication)</b>		
Examiner Initial	Desig. ID	Document
	ASS	M. Fuse et al.; "Performance of Poly-Si Thin Film Transistors Fabricated by Excimer-Laser Annealing of SiH <sub>4</sub> - and Si <sub>2</sub> H <sub>6</sub> - Source Low Pressure Vapor Deposited a-Si Films with or without Solid-Phase Crystallization"; <u>Solid State Phenomena</u> , vols. 37-38; pp. 565-570 (1994)
	ATT	Rafael Reif et al.; "Plasma-Enhanced Chemical Vapor Deposition"; <u>Thin Film Processes II</u> ; pp. 537-541; (1991)
	AUU	Sorab Ghandhi.; "Thermal Oxidation of Gallium Arsenide"; <u>VLSI Fabrication Principles - Silicon and Gallium Arsenide</u> ; 2 <sup>nd</sup> Edition, pp. 484, 485, 533-535
	AVV	S.M. Sze; <u>VLSI Technology</u> ; 2 <sup>nd</sup> Edition, pp. 85-86, 266-267 (1988)
	AWW	Hongyong Zhang et al.; "KrF Excimer Laser Annealed TFT with Very High Field-Effect Mobility of 329 cm <sup>2</sup> /v · s"; <u>IEEE Electron Device Letters</u> ; vol. 13, no. 5; pp. 297-299 (May 1992)

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